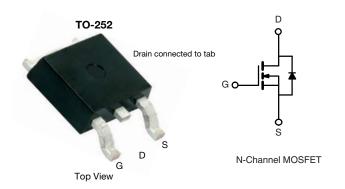


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Vishay Siliconix

# Automotive N-Channel 300 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	300			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.330			
I <sub>D</sub> (A)	10			
Configuration	Single			



#### **FEATURES**

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R<sub>a</sub> tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



**FREE** 

ORDERING INFORMATION			
Package	TO-252		
Lead (Pb)-free and Halogen-free	SQD10N30-330H-GE3		

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	$V_{DS}$	300	V		
Gate-Source Voltage	$V_{GS}$	± 30	V		
Continuous Drain Current	T <sub>C</sub> = 25 °C	I-	10	A	
Continuous Drain Current	T <sub>C</sub> = 125 °C	l <sub>D</sub>	5		
Continuous Source Current (Diode Conduction) a		I <sub>S</sub>	50		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	16			
Single Pulse Avalanche Current <sup>e</sup>	L = 0.05 mH	I <sub>AS</sub>	12.65		
Single Pulse Avalanche Energy <sup>e</sup>	L = 0.03 IIII	E <sub>AS</sub>	4	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	107	W	
Maximum i Owei Dissipation -	T <sub>C</sub> = 125 °C	$P_{D}$	35	VV	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount c	$R_{thJA}$	50	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.4	C/VV	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300 \,\mu\text{s}$ , duty cycle  $\leq 2 \,\%$ .
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.
- e.  $1.5 \text{ k}\Omega$  resistance in series with the gate.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	•							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		300	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		3.8	4.4	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 30 \text{ V}$		-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 300 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 300 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 300 V, T <sub>J</sub> = 175 °C	-	-	250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 14 A	-	0.275	0.330		
Drain-Source On-State Resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 14 A, T <sub>J</sub> = 125 °C	-	-	0.733	Ω	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 14 A, T <sub>J</sub> = 175 °C	-	-	1.000		
Forward Transconductance b g <sub>fs</sub> V <sub>Ds</sub>			= 15 V, I <sub>D</sub> = 14 A	-	26	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	1749	2190		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	112	140	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	44	55		
Total Gate Charge <sup>c</sup>	Qg			-	31	47		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 150 \text{ V}, I_D = 7 \text{ A}$	-	8	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	9.6	-		
Gate Resistance	R <sub>g</sub>		f = 1 MHz		0.8	3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>				10	15		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 150 V, $R_L$ = 21 $\Omega$ $I_D \cong 7$ A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		-	18	28	ns	
Turn-Off Delay Time °	t <sub>d(off)</sub>			-	20	30		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12		
Source-Drain Diode Ratings and Chara	cteristics b	•						
Pulsed Current a	I <sub>SM</sub>			-	-	16	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 25 A, V <sub>GS</sub> = 0 V		_	0.9	1.5	V	
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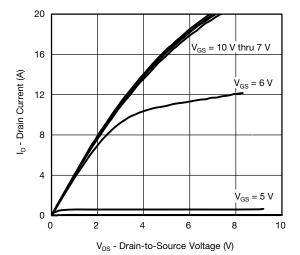
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

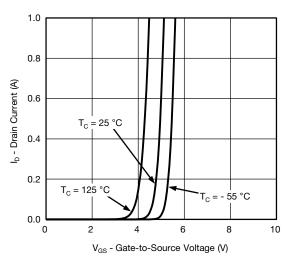
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



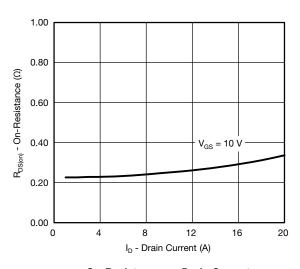
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



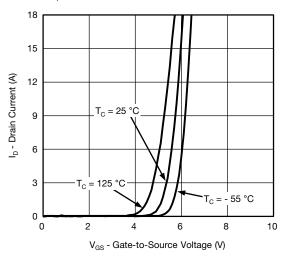
#### **Output Characteristics**



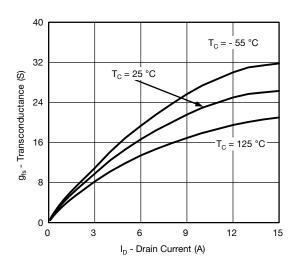
### Transfer Characteristics



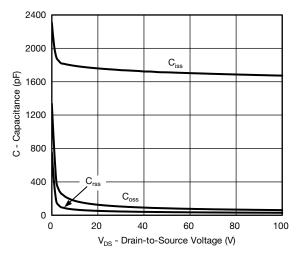
On-Resistance vs. Drain Current



#### **Transfer Characteristics**



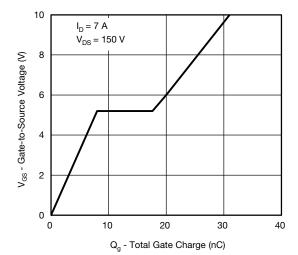
#### Transconductance



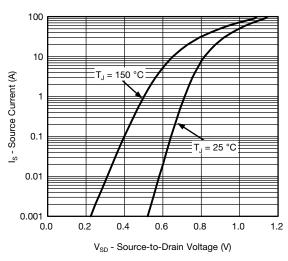
Capacitance



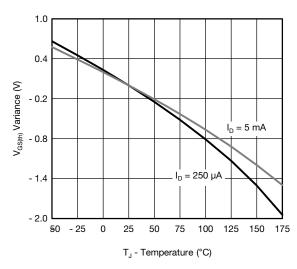
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



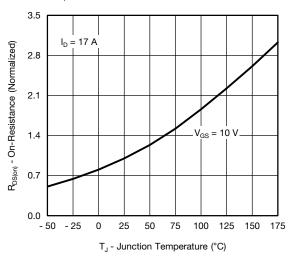
#### **Gate Charge**



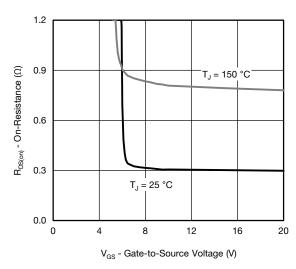
## Source Drain Diode Forward Voltage



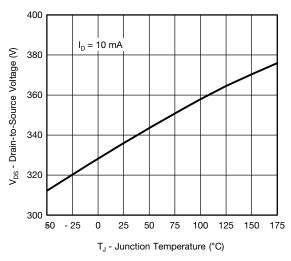
**Threshold Voltage** 



#### On-Resistance vs. Junction Temperature



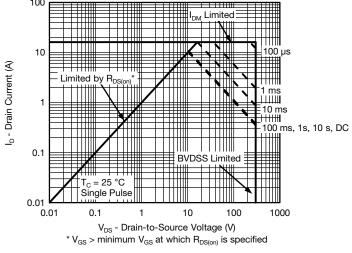
#### On-Resistance vs. Gate-to-Source Voltage



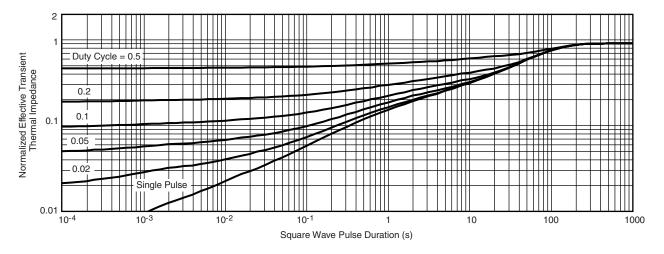
Drain Source Breakdown vs. Junction Temperature



### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



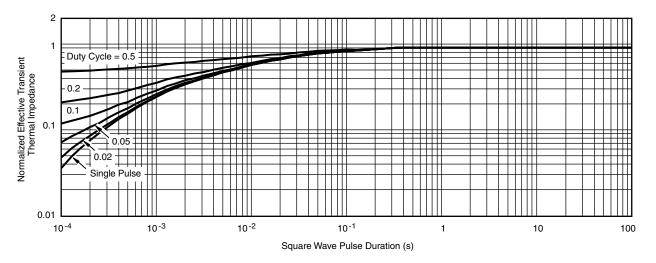
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg267070">www.vishay.com/ppg267070</a>.



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REVISION HISTORY <sup>a</sup>					
REVISION	DATE	DESCRIPTION OF CHANGE			
В	26-Feb-2015	UIS changed			
С	04-May-2015	R <sub>g</sub> , C <sub>iss</sub> and t <sub>r</sub> updated			

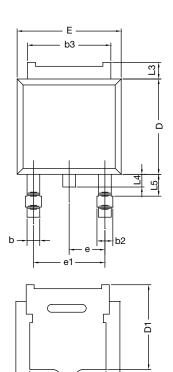
#### Note

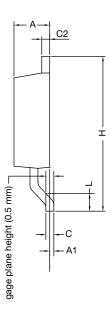
a. As of April 2014



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## **TO-252AA Case Outline**





	MILLIN	METERS	INC	HES		
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	4.10	-	0.161	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28	BSC	0.090	0.090 BSC		
e1	4.56 BSC		0.180 BSC			
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.01	1.52	0.040	0.060		
ECN: T13-0592-Rev. A, 02-Sep-13						

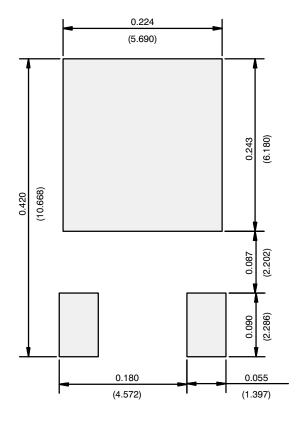
### DWG: 6019

Note

• Dimension L3 is for reference only.



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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